

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14491	(high near10 density near10 plasma)	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 12:03
L2	8447	1 and (reactor chamber)	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 11:54
L3	379	2 and (deuterium tritium deuterat\$3 tritiat\$3 (heavy near5 hydrogen))	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 14:54
L4	293	3 and (oxide insulat\$3 dielectric (silicon near5 (oxide dioxide)) ("Si" adj3 "O. sub.2"))	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 14:53
L5	134	4 and semiconductor	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 11:24
L6	4814	(high near10 density near10 plasma)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 11:53
L7	1741	6 and (reactor chamber)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 11:54
L8	6	7 and (deuterium tritium deuterat\$3 tritiat\$3 (heavy near5 hydrogen))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 11:55
L10	0	("("Si"adj"D"adj"H)").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/07/18 12:02
L11	264	("Si" adj3 "D" adj3 "H")	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 12:05
L12	0	11 and (high near10 density near10 plasma)	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 12:04
L13	2	11 and plasma	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 12:04
L14	7	("Si" adj3 "D" adj3 "H")	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 12:17
L17	2799021	(minimiz\$3 near5 (void gap) or (fill\$3 gap) treat\$3 passivat\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:01

L18	991207	17 and (oxide insulat\$3 dielectric (silicon near5 (oxide dioxide)) ("Si" adj3 "O. sub.2"))	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:01
L19	14020	18 and (deuterium tritium deuterat\$3 tritiat\$3 (heavy near5 hydrogen))	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:01
L20	2352	19 and (semiconductor (semi near3 conductt\$3) wafer)	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 14:56
L21	89	19 and (HDP (high near5 density near5 plama))	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:02
L22	77	21 and 20	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 14:57
L23	2251736	(minimiz\$3 near5 (void gap) or (fill\$3 gap) treat\$3 passivat\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 15:01
L24	270218	23 and (oxide insulat\$3 dielectric (silicon near5 (oxide dioxide)) ("Si" adj3 "O. sub.2"))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 15:01
L25	225	24 and (deuterium tritium deuterat\$3 tritiat\$3 (heavy near5 hydrogen))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 15:01
L26	19	25 and (CVD plasma)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/18 15:06
L27	1401	20 AND plasma	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:26
L28	295	27 and "438"/\$.ccls.	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:27
L29	42	27 and "430"/\$.ccls.	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:27
L30	74	27 and "427"/\$.ccls.	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:27
L31	360	27 and "257"/\$.ccls.	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 15:28
L32	505	28 29 30 31	US-PGPU B; USPAT; USOCR	OR	ON	2005/07/18 16:08